	Hits	Search Text
1	0	OLED and ((n+m) with subframes)
2	28	OLED and (subframes)
3	51	OLED and (plurality near5 frames)
4	0	OLED and (subframes)
5	0	OLED and (plurality near5 frames)
6	4	OLED and (subframes)
7	11	OLED and (plurality near5 frames)
8	14	OLED and (plurality with frames)
9	0	(pseudo adj4 contours) and (pluraliy adj3 frames)
10	3	(pseudo adj4 contours) and subframes
11	6	(pseudo adj4 contours) and subframes
12	9	(pseudo adj4 contours) and subframes
13	21	(pseudo adj4 contours) and subfields
14	18	((pseudo adj4 contours) and subfields) not ((pseudo adj4 contours) and subframes)
15	0	(pseudo adj4 contours) and subfields and OLED
16	0	(pseudo adj4 contours) and subfields and OLED
17	30	(pseudo adj4 contours) and subfields
18	4	(pseudo adj4 contours) and subfields and LED
19	0	OLED and (three adj5 TFT)
20	75	OLED and TFT
21	20	OLED near5 TFT
22	0	OLED and ((n+m) near5 subframes)
23	0	OLED and TFT and erase
24	0	OLED and TFT and eras\$%
25	1	OLED and (erasi\$5 near5 TFT)
26	6	("5247190" "5399502" "5990629" "6246180" "6292183" "6335716").PN.
27	1	OLED and (erasi\$5 with TFT)
28	1	OLED and (erasi\$5 same TFT)
29	0	LED and (erasi\$5 same TFT)
30	6	EL and (erasi\$5 same TFT)
31	4	EL and (erasi\$5 with TFT)

l DBs	
1 US-PGPUB; USPAT	Γ
2 US-PGPUB; USPAT	
3 US-PGPUB; USPA	-
 US-PGPUB; USPA US-PGPUB; USPA EPO; JPO; DERWE IBM_TDB 	ENT;
5 EPO; JPO; DERWE	ENT;
6 USPAT 7 USPAT	
7 USPAT	
8 USPAT	
9 USPAT	
10 USPAT	
EPO; JPO; DERWEIBM_TDB	ENT;
12 US-PGPUB; USPAT	Γ
13 USPAT	
14 USPAT	
EPO; JPO; DERWEIBM_TDB	ENT;
16 USPAT	
EPO; JPO; DERWEIBM_TDB	ENT;
18 USPAT	
19 USPAT	
20 USPAT	
21 USPAT	
22 US-PGPUB; USPA	
23 USPAT	
24 USPAT	
25 USPAT	
26 USPAT	_
27 USPAT	
28 USPAT	
29 USPAT	
30 USPAT	
31 USPAT	

	Hits	Search Text
32	2	EL and (erasi\$5 same TFT)
33	10	(EL OLED LED plasma)and (erasi\$5 same TFT)
34	6	(EL OLED LED)and (erasi\$5 same TFT)
35	0	((EL OLED LED)and (erasi\$5 same TFT)) not ((EL OLED LED plasma)and (erasi\$5 same TFT))
36	4	((EL OLED LED plasma)and (erasi\$5 same TFT)) not ((EL OLED LED)and (erasi\$5 same TFT))
37	1	"6373454".pn.
38	1	"6373454".URPN.
39	5	("5302966" "5652600" "6034659" "6091203" "6229506").PN.
40	1	"5302966".pn.
41	34	"5302966".URPN.
42	156	EL and (erasi\$5 same line)
43	2	EL with (erasi\$5 adj2 line)
44	13	EL and (erasi\$5 adj2 line)
45	13	EL and (erasi\$5 same line)
46	8	EL with (erasi\$5 near5 line)
47	1	"6040819".pn.
48	3	"6040819".URPN.
49	3	("4827255" "5479188" "5539432").PN.
50	9096	TFT and (crystalline adj3 semiconductor near5 film) and (gate adj3 insulating adj3 film) and (gate adj3 electrodes) and (channel adj3 regions)I and (impurity near3 regions)
51	9096	TFT and (crystalline adj3 semiconductor near5 film) and (gate adj3 insulating adj3 film) and (gate adj3 electrodes) and (channel adj3 regions)l and (impurity near3 regions)
52	8391	TFT and (crystalline adj3 semiconductor near5 film) same (gate adj3 insulating adj3 film) same (gate adj3 electrodes) same (channel adj3 regions)I and (impurity near3 regions)
53	8358	TFT same (crystalline adj3 semiconductor near5 film) same (gate adj3 insulating adj3 film) same (gate adj3 electrodes) same (channel adj3 regions)l and (impurity near3 regions)

	DBs
22	EPO; JPO; DERWENT;
32	IBM_TDB
33	USPAT
34	USPAT
35	USPAT
36	USPAT
37	USPAT
38	USPAT
39	USPAT
40	USPAT
41	USPAT
42	USPAT
43	USPAT
44	USPAT
45	EPO; JPO; DERWENT;
4 5	IBM_TDB
46	USPAT
47	US-PGPUB; USPAT
48	USPAT
49	USPAT
50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text
54	8349	TFT with (crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film) with (gate adj3 electrodes) with (channel adj3 regions)I and (impurity near3 regions)
55	5690	TFT with (crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film) with (gate adj3 electrodes) with (channel adj3 regions) and (impurity near3 regions)
56	230	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) near5 (gate adj3 electrodes) with (channel adj3 regions) with (impurity near3 regions)
57	113	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) near5 (gate adj3 electrodes) near7 (channel adj3 regions)I near7 (impurity near3 regions)
58	0	TFT near8 ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) near5 (gate adj3 electrodes) near7 (channel adj3 regions)l near7 ((impurity near3 regions) adj4 (crystalline adj3 semiconductor near5 film) adj4 (channel adj3 regions))
59	0	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) near5 (gate adj3 electrodes) near7 (channel adj3 regions)l near7 ((impurity near3 regions) adj4 (crystalline adj3 semiconductor near5 film) adj4 (channel adj3 regions))
60	0	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) near5 (gate adj3 electrodes) near7 (channel adj3 regions)l with ((impurity near3 regions) adj4 (crystalline adj3 semiconductor near5 film) adj4 (channel adj3 regions))
61	0	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) near7 (channel adj3 regions)l with ((impurity near3 regions) adj4 (crystalline adj3 semiconductor near5 film) adj4 (channel adj3 regions))

	DBs
54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
55	USPAT
56	USPAT
57	USPAT
58	USPAT
59	USPAT
60	USPAT
61	USPAT

	Hits	Search Text
62	0	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) near7 (channel adj3 regions) with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions))
63	113	TFT near8 ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) near5 (gate adj3 electrodes) near7 (channel adj3 regions) near7 (impurity near3 regions)
64	2	TFT with ((crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) with (channel adj3 regions)l with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions))
65	6	TFT with ((crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) with (channel adj3 regions)I with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions))
66	38	TFT and ((crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) with (channel adj3 regions)I with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions))
67	38	TFT and ((crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) with (channel adj3 regions)! with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions)) and ((impurity adj3 region) near3 (pair near4 (impurity adj3 region)))

	DBs
62	USPAT
63	USPAT
64	USPAT
65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text
68	38	TFT and ((crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) with (channel adj3 regions)l with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions)) and ((impurity adj3 region) near3 (pair adj3 (impurity adj3 region)))
69	38	TFT and ((crystalline adj3 semiconductor near5 film) with (gate adj3 insulating adj3 film)) with (gate adj3 electrodes) with (channel adj3 regions)l with ((impurity near3 regions) near5 (crystalline adj3 semiconductor near5 film) near5 (channel adj3 regions)) and ((impurity adj3 region) near3 between near3 (pair adj3 (impurity adj3 region)))
70	191	((impurity adj3 region) near3 between near3 (pair adj3 (impurity adj3 region)))
71	3	((impurity adj3 region) adj between adj (pair adj3 (impurity adj3 region)))
72	16	((impurity adj3 region) adj2 between adj2 (pair adj3 (impurity adj3 region)))
73	4	((impurity adj3 region) adj2 between adj2 (pair adj3 (impurity adj3 region))) and TFT
74	0	((impurity adj3 region) adj2 between adj2 (pair adj3 (impurity adj3 region))) and TFT and ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film))
75	4	((impurity adj3 region) with between with (pair adj3 (impurity adj3 region))) and TFT and ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film))
76	0	"T4773738.pn"
77	2	"4773738".pn.

	DBs
68	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
70	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
73	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text
78	2	"5091722".pn.
79	2	"5200846".pn.
80	2	"5225823".pn.
81	2	"5349366".pn.
82	2	"5414442".pn.
83	2	"5424752".pn.
84	2	"5471225".pn.
85	2	"5479283".pn.
86	2	"5583534".pn.
87	2	"5600169".pn.
88	2	"5642129".pn.
89	2	"5712652".pn.
90	2	"5798746".pn.

	DBs
	US-PGPUB; USPAT; USOCR;
78	EPO; JPO; DERWENT;
	IBM_TDB
70	US-PGPUB; USPAT; USOCR;
79	EPO; JPO; DERWENT; IBM_TDB
-	US-PGPUB; USPAT; USOCR;
80	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
81	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
82	EPO; JPO; DERWENT;
	IBM_TDB
0.7	US-PGPUB; USPAT; USOCR;
83	EPO; JPO; DERWENT; IBM TDB
<u> </u>	US-PGPUB; USPAT; USOCR;
84	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
85	EPO; JPO; DERWENT;
ļ	IBM_TDB
_	US-PGPUB; USPAT; USOCR;
86	EPO; JPO; DERWENT;
	IBM_TDB
87	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;
\	IBM_TDB
	US-PGPUB; USPAT; USOCR;
88	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
89	EPO; JPO; DERWENT;
-	IBM_TDB
00	US-PGPUB; USPAT; USOCR;
90	EPO; JPO; DERWENT; IBM_TDB
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	Hits	Search Text
91	2	"6034659".pn.
92	2	"6157356".pn.
93	2	"6215466".pn.
94	2	"6452341".pn.
95	2	"6542138".pn.
96	2	"6563480".pn.
97	2	"6778152".pn.
98	2	"6791129".pn.
99	2	"5767828".pn.
100	2	"5969710".pn.
101	2	"5986640".pn.
102	2	"6689492".pn.
103	3	"6617644".pn.

	DBs
	US-PGPUB; USPAT; USOCR;
91	EPO; JPO; DERWENT;
	IBM_TDB
92	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;
32	IBM TDB
	US-PGPUB; USPAT; USOCR;
93	EPO; JPO; DERWENT;
-	IBM_TDB
	US-PGPUB; USPAT; USOCR;
94	EPO; JPO; DERWENT;
	IBM_TDB US-PGPUB; USPAT; USOCR;
95	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
96	EPO; JPO; DERWENT;
	IBM_TDB
0.7	US-PGPUB; USPAT; USOCR;
97	EPO; JPO; DERWENT; IBM TDB
	US-PGPUB; USPAT; USOCR;
98	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
99	EPO; JPO; DERWENT;
	IBM_TDB US-PGPUB; USPAT; USOCR;
100	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
101	1
	IBM_TDB
102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;
102	IBM TDB
	US-PGPUB; USPAT; USOCR;
103	EPO; JPO; DERWENT;
	IBM_TDB

	Hits	Search Text
104	2	"6236064".pn.
105	2	"5729308".pn.
106	2	"6184559".pn.
107	2	"6246179".pn.
108	2	"6794675".pn.
109	2	"5412493".pn.
110	663	(345/76).CCLS.
111	395	(345/82).CCLS.
112	543	(345/92).CCLS.
113	985	(345/204).CCLS.
114	209	(345/206).CCLS.
115	583	(345/690).CCLS.
116	54	(345/692).CCLS.
117	0	(pseudo adj4 contours) same (pluraliy adj3 frames)
118	27	(pseudo adj4 contours) same subfields
119	23	(pseudo adj4 contours) with subfields
120	36	EL same (erasi\$5 same line)
121	29	EL same (erasi\$5 with line\$4)
122	119	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) adj5 (gate adj3 electrodes) adj7 (channel adj3 regions)! near7 (impurity near3 regions)
123	54	TFT with ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film)) adj5 (gate adj3 electrodes) adj7 (channel adj3 regions)! adj5 (impurity near3 regions)

	DBs
	US-PGPUB; USPAT; USOCR;
1	EPO; JPO; DERWENT;
1	IBM_TDB
	US-PGPUB; USPAT; USOCR;
105	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
106	EPO; JPO; DERWENT;
	IBM_TDB
	US-PGPUB; USPAT; USOCR;
107	EPO; JPO; DERWENT;
	IBM_TDB
400	US-PGPUB; USPAT; USOCR;
108	EPO; JPO; DERWENT;
	IBM_TDB
109	US-PGPUB; USPAT; USOCR;
109	EPO; JPO; DERWENT; IBM_TDB
110	USPAT
\vdash	USPAT
	USPAT
	USPAT
	USPAT
	USPAT
	USPAT
	USPAT
	EPO; JPO; DERWENT;
118	IBM TDB
440	EPO; JPO; DERWENT;
119	IBM_TDB
120	USPAT
121	USPAT
122	USPAT
4.00	LICDAT
123	USPAT
L	L

	Hits	Search Text
124	0	(three adj3 TFT\$4) with EL same (subframe44 subfield\$4)
125	6	(three adj3 TFT\$4) with EL
126	12	(three adj3 TFT\$4) same EL
127	0	(three adj3 TFT\$4) same EL same (subframe44 subfield\$4)
128	0	(three adj3 TFT\$4) and EL same (subframe44 subfield\$4)
129	0	(three adj3 TFT\$4) and EL and (subframe44 subfield\$4)
130	5	((impurity adj3 region) same between same (pair adj3 (impurity adj3 region))) and TFT and ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film))
131	5	((impurity adj3 region) and between same (pair adj3 (impurity adj3 region))) and TFT and ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film))
132	7	((impurity adj3 region) and between and (pair adj3 (impurity adj3 region))) and TFT and ((crystalline adj3 semiconductor near5 film) adj3 (gate adj3 insulating adj3 film))

	DBs
124	USPAT
125	USPAT
126	USPAT
127	USPAT
128	USPAT
129	USPAT
130	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
131	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
132	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB